

CLEAN COPY OF AMENDED CLAIMS:

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1. (Twice Amended) A planarization method of inter-layer dielectrics, comprising the steps of:

- providing a semiconductor substrate including a field oxide, a source, a drain, and a gate formed thereon;
- forming a dielectric layer used as an inter-layer dielectric on said semiconductor substrate, lapping said dielectric layer by means of a chemical mechanical polishing; and
- forming on said lapped dielectric layer a cap layer of a refractive index larger than 1.6 and having a thickness thereof in the range of 300-2000Å.

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5. (Amended) The planarization method of inter-layer dielectrics as claimed in Claim 1, wherein said cap layer is a silicon nitride layer translucent to ultra-violet light.

B³ 6. (Twice Amended) The planarization method of inter-layer dielectrics as claimed in Claim 1, wherein said cap layer is a silicon nitrogen-oxide layer translucent to ultra-violet light.

B⁴ 9. (Twice Amended) A planarization method of inter-metal dielectrics, comprising the steps of:
providing a semiconductor substrate having a plurality of metal-interconnects formed thereon;
forming a dielectric layer used as an inter-metal dielectric on said substrate, lapping said dielectric layer by means of a chemical mechanical polishing; and
forming on said lapped dielectric layer a cap layer of a refractive index larger than 1.6 and having a thickness thereof in the range of 300-2000Å.

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B⁵ 16. (Amended) The planarization method of inter-metal dielectrics as claimed in Claim 9, wherein said cap layer is a silicon nitride layer translucent to ultra-violet light.

B⁶ 17. (Twice Amended) The planarization method of inter-metal dielectrics as claimed in Claim 9, wherein said cap layer is a silicon nitrogen-oxide layer translucent to ultra-violet light.